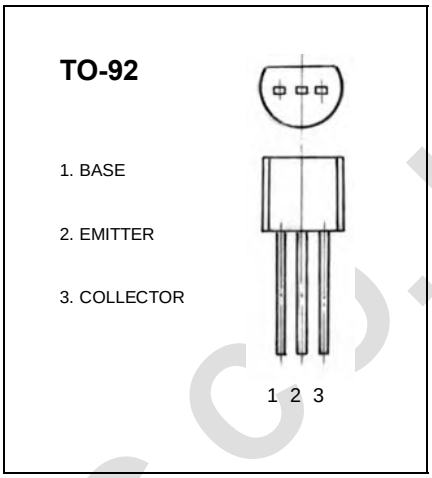
MPSH10/11 TRANSISTOR (NPN)



FEATURES

Power dissipation

$P_{CM:}$ 0.35 W (Tamb=25℃)

Collector current

$I_{CM:}$ 0.05 A

Collector-base voltage

$V_{(BR)CBO}$: 30 V

Operating and storage junction temperature range

T_J, T_{stg}: -55℃ to +150℃

ELECTRICAL CHARACTERISTICS (Tamb=25℃ unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	$V(BR)_{CBO}$	I_C= 100μA, I_E=0	30			V
Collector-emitter breakdown voltage	$V(BR)_{CEO}$	I_C= 1mA, I_B=0	25			V
Emitter-base breakdown voltage	$V(BR)_{EBO}$	I_E= 10μA, I_C=0	3			V
Collector cut-off current	I_{CBO}	V_{CB}= 25V, I_E=0			0.1	μA
Collector cut-off current	I_{CEO}	V_{CE}= 20V, I_B=0			0.2	μA
Emitter cut-off current	I_{EBO}	V_{EB}= 2V, I_C=0			0.1	μA
DC current gain	h_{FE}	V_{CE}= 10V, I_C= 4mA	60		200	
Collector-emitter saturation voltage	V_{CE}(sat)	I_C=4mA, I_B=0.4mA			0.5	V
Collector-emitter voltage	V_{BE}(on)	V_{CE}=10V, I_C=4mA			0.95	V
Transition frequency	f_T	V_{CE}= 10V, I_C=4mA f =100MHz	650			MHz